

B1
C1
cont'd

an annular magnet array disposed within the chamber to form a stationary [substantially parallel] magnetic field that is substantially parallel to [at] the surface of the substrate support.

B2

5. (Twice Amended) The apparatus of claim [4] 3, wherein the target comprises a nickel/iron alloy.

6. (Twice Amended) [An] The apparatus of claim 1 [for depositing a magnetic film, comprising:] wherein the

[a sputtering chamber containing a] target and [a] the substrate supporting surface are separated by a distance of at least about 50 mm [; and

a magnet array disposed within the chamber to form a parallel magnetic field at the substrate supporting surface].

B3
sub
62

15. (Twice Amended) A method for depositing a magnetic film within a sputtering chamber containing a target and a substrate, comprising:

sputtering the target onto a surface of the substrate at a pressure less than about 15 mTorr;

collimating sputtering of the target with a grounded collimator disposed between the target and the substrate; and

[providing] generating a [parallel] stationary magnetic field [at] that is substantially parallel to the surface of the substrate during sputtering using an annular magnet array disposed within the sputtering chamber.

B4

18. (Twice Amended) The method of claim [17] 16, wherein the target and the surface of the substrate are maintained at a distance of at least about 50 mm during sputtering.